

Citations for Ion : **Se**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1964	Wikner, E. G. Horiye, H. Nichols, D. K. 'Elastic Versus Inelastic Energy Loss of Recoil Germanium and Silicon Atoms' <i>Phys. Rev. A, 136, 1428-32 (1964)</i> <i>Comment : S, Eta(Epsilon). 68-157 keV Si -> Si, 19-36 keV Ge -> Ge</i>	1964-Wikn
1968	Bowman, W. W. Lanzafame, F. M. Cline, C. K. Yu, Yu-Wen Blann, M. 'Recoil Ranges of 0.2 - 5.2 MeV Ions in Vanadium, Nickel, Iron, Zirconium and Gold.' <i>Phys. Rev., 165, 485-93 (1968)</i> <i>Comment : R, dR. Ion(ZI=12-81, E=0.22-5.2 MeV) -> V, Ni, Zr, Au</i>	1968-Bowm
1970	Santry, D. C. Sitter, C. W. 'Range and Retention Studies of 40-keV Ions in Solids, in H' <i>Wagner, W. Walcher (Ed.) Proc. Int. Conf. Elmag. Isotope Separators and Their Techniques. Marburg, P. 505-24 (1970)</i> <i>Comment : R, dR. 40 keV C, O, P, Co, Tl, Na, P, Co, Zn, Se, Kr, Hf, Cs, Ag, I, Xe -> Au, W, WO3</i>	1970-Sant
1972	Jokic, T. 'Xenon Ion Penetration in Gold' <i>6th Yugoslav Symposium on Physics of Ionized Gases, 97-100 (1972)</i> <i>Comment : R, dR. 20-100 keV Xe -> Au</i>	1972-Joki
1973	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. 'Range Distributions of Implanted Ions in SiO ₂ , Si ₃ N ₄ , and Al ₂ O ₃ ' <i>Appl. Phys. Letters, 22, 490-92 (1973)</i> <i>Comment : R, dR. Zn, Ga, As, Se, Cd, Te (140-300 keV) -> SiO₂, Si₃N₄, Al₂O₃</i>	1973-Chu
1973	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. 'Ranges and Distributions of Ions Implanted into Dielectrics' <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 225-41 (1973)</i> <i>Comment : R.dR. (140-300 keV) Zn, Ga, As, Se, Cd, Te, Zn -> Si, Si₃N₄, Al₂O₃</i>	1973-Chu 2
1974	Blok, H. Kiely, F. M. Pate, B. D. Hanappe, F. Pelier, J. 'Further Measurement of the Track Length of Heavy Ions in Mica' <i>Nucl. Inst. Methods, 119, 307-12 (1974)</i> <i>Comment : R. (2.7-160 MeV) Al, Ar, Ca, Cr, Ni, Se, Kr, Ag -> Mica</i>	1974-Blok
1975	Ambridge, T. Heckingbottom, R. 'Effect of Dual Implants into GaAs' <i>Elec. Letters, 11 (1975)</i> <i>Comment : R. 350 keV Se, Ga -> GaAs</i>	1975-Ambr
1976	Sood, D. K. Dearnaley, G. 'Ion-Implanted Surface Alloys in Copper and Aluminum' <i>G. Carter, J. S. Colligon, W. A. Grant (Ed.): Appl. of Ion Beams to Materials. Inst. of Physics Conf. Ser. No. 28, 169-203 (1976)</i> <i>Comment : R. (150-300) keV Au, Mo, Bi, Ta, Mo, Gd, Bi, Cu, Rb, Ru, Cs, Ce, Eu, Ag, Cu, Se, Au -> Cu; Rb, Cd, Cs -> Al.</i>	1976-Sood

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1977	<p>Surridge, R. K. Sealy, B. J. 'A Comparison of Sn-, Ge-, Se-, and Te-Ion-Implanted GaAs' <i>Appl. Phys.</i>, 10, 911-917 (1977)</p> <p><i>Comment</i> : R. 200 And 300 keV Sn, Ge, Se, Te -> GaAs</p>	1977-Surr
1977	<p>Surridge, R. K. Sealy, B. J. D'Cruz, A. D. E. Stephens, K. G. 'Annealing Kinetics of Donor Ions Implanted into GaAs' <i>Gallium Arsenide and Related Compounds (Edinburgh)</i>, Ed. by C. Hilsum, 161-167 (1977)</p> <p><i>Comment</i> : R. 200 keV Se, Sn -> GaAs</p>	1977-Surr2
1978	<p>Lidow, A. Gibbons, J. F. Deline, V. R. Evans, C. A. 'Fast Diffusion of Elevated-Temperature Ion-Implanted Se in GaAs as Measured by Secondary Ion Mass Spectrometry' <i>Appl. Phys. Letters</i>, 32, 149-151 (1978)</p> <p><i>Comment</i> : R. 120, 150 keV Se -> As</p>	1978-Lido
1980	<p>Gamo, K. Yagita, H. Takai, M. Namba, S. Takigawa, M. 'Ion Implantation of Zn, Se, and Cd in BP Crystals' <i>Rad. Effects</i>, 47, 45-50 (1980)</p> <p><i>Comment</i> : R, dR. 70 keV Zn, Se, Cd -> BP (crystal)</p>	1980-Gamo